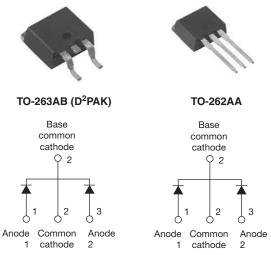
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VS-MURB1020CTHM3, VS-MURB1020CT-1HM3

Vishay Semiconductors

Ultrafast Rectifier, 2 x 5 A FRED Pt[®]



VS-MURB1020CTHM3

VS-MURB1020CT-1HM3

PRODUCT SUMMARY					
Package	TO-263AB (D ² PAK), TO-262AA				
I _{F(AV)}	2 x 5 A				
V _R	200 V				
V _F at I _F	0.87				
t _{rr} (typ.)	19 ns				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
 HALOG
- AEC-Q101 qualified
- Meets JESD 201 class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average rectified featured current per leg		1		5			
Average rectified forward current total device	otal device	IF(AV)	Rated V _R , T _C = 149 °C	10	^		
Non-repetitive peak surge current per leg		I _{FSM}		50	A		
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 149 °C	10			
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage		I _F = 5 A, T _J = 25 °C	-	0.99	1.08	v	
	V _F	I _F = 5 A, T _J = 125 °C	-	0.87	0.99	v	
		I _F = 10 A, T _J = 25 °C	-	1.12	1.25		
		I _F = 10 A, T _J = 125 °C	-	1.02	1.20		
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	10	μA	
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μΑ	
Junction capacitance	CT	V _R = 200 V	-	8	-	pF	
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8.0	-	nH	



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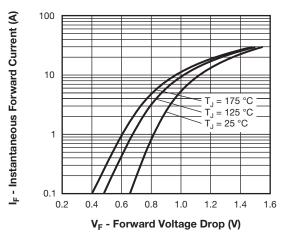
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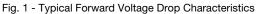
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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 10$	00 A/µs, V _R = 30 V	-	19	-	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 5 A dI _F /dt = 200 A/μs V _R = 160 V	-	24	-	ns
		T _J = 125 °C		-	35	-	
Deels receivers ourrent		T _J = 25 °C		-	3.3	-	٨
Peak recovery current	I _{RRM}	T _J = 125 °C		-	5.0	-	A
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	33	-	nC
		T _J = 125 °C		-	76	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	-	5	
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-263AB (D ² PAK)	MURB1020CTH			
		Case style TO-262AA		MURB10	20CT-1H	





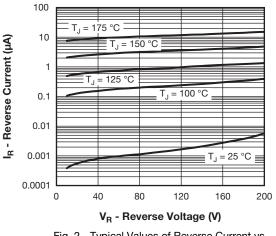


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Revision: 02-Feb-16

2

Document Number: 95807

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VS-MURB1020CTHM3, VS-MURB1020CT-1HM3

Vishay Semiconductors

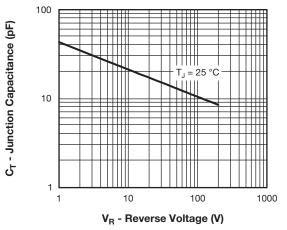
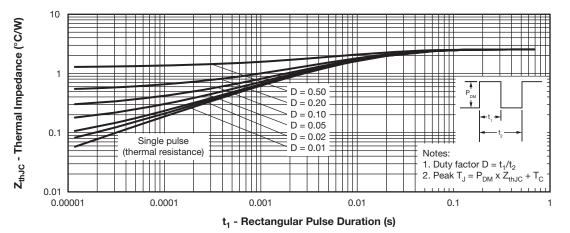
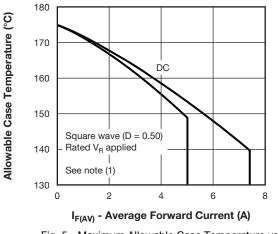


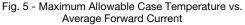
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





Average Power Loss (W)





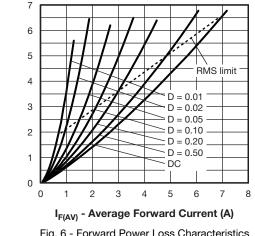


Fig. 6 - Forward Power Loss Characteristics

Revision: 02-Feb-16

3

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VS-MURB1020CTHM3, VS-MURB1020CT-1HM3 ISHAY www.vishay.com **Vishay Semiconductors** 50 160 10 A = 5 A 140 $I_{F} = 10 \text{ A}$ 40 120 = 5 A 100 Q_{rr} (nC) t_{rr} (ns) 30 80 60 20 40 V_R = 160 V V_R = 160 V = 125 °C -T₁ = 125 °C Τ. 20 T_j = 25 °C = 25 °C ТJ 10 0 100 1000 100 1000 dl_F/dt (A/µs) dl_F/dt (A/µs) Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/\mbox{D}) \mbox{ (see fig. 6);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); } \mbox{I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{Rated V}_{R} \end{array}$

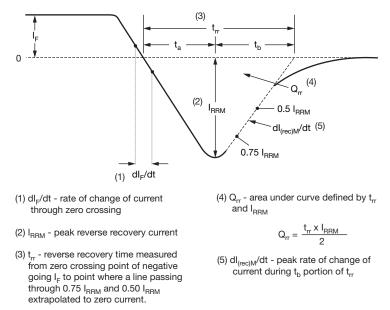


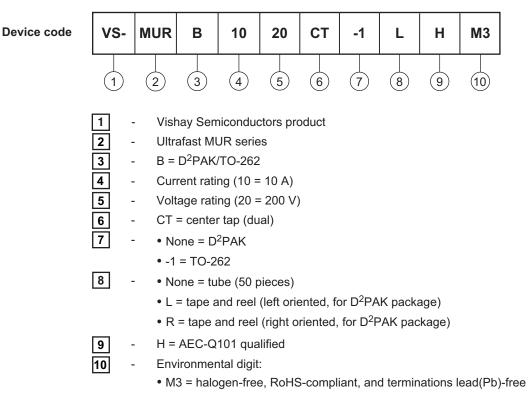
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-MURB1020CTHM3, VS-MURB1020CT-1HM3

Vishay Semiconductors

ORDERING INFORMATION TABLE

www.vishay.com



ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-MURB1020CTHM3	50	1000	Antistatic plastic tube			
VS-MURB1020CT-1HM3	50	1000	Antistatic plastic tube			
VS-MURB1020CTLHM3	800	800	13" diameter reel			
VS-MURB1020CTRHM3	800	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046			
Dimensions	TO-262AA	www.vishay.com/doc?95419			
Dout moulting information	TO-263AB (D ² PAK)	www.vishay.com/doc?95444			
Part marking information	TO-262AA	www.vishay.com/doc?95443			
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032			

5

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		ERS INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 08-Jul-15

1

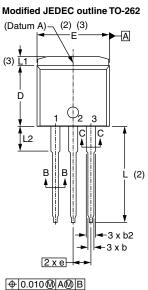


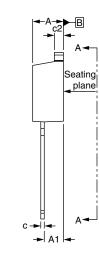
Outline Dimensions

Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches

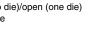


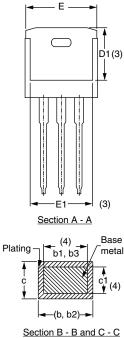


Lead assignments



Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode





Scale: None

CVMDOI	MILLIM	ETERS	INC	NOTES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.10	0 BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

Revision: 04-Oct-10

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

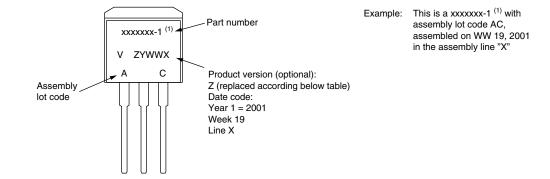
⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

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TO-262



Note

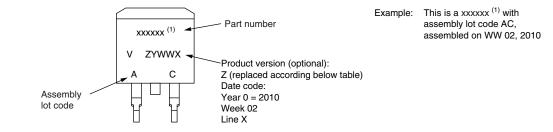
⁽¹⁾ If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION		
A Termination lead (Pb)-free			
B Totally lead (Pb)-free			
E	RoHS-compliant and termination lead (Pb)-free		
F	RoHS-compliant and totally lead (Pb)-free		
М	Halogen-free, RoHS-compliant and termination lead (Pb)-free		
Ν	Halogen-free, RoHS-compliant and totally lead (Pb)-free		
G	Green		



Vishay Semiconductors

D²PAK



Note

⁽¹⁾ If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION
A	Termination lead (Pb)-free
В	Totally lead (Pb)-free
E	RoHS-compliant and termination lead (Pb)-free
F	RoHS-compliant and totally lead (Pb)-free
М	Halogen-free, RoHS-compliant, and termination lead (Pb)-free
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free
G	Green



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